2SC3934G

Silicon NPN epitaxial planar type

For high-frequency wide-band low-noise amplification

■ Features

- High transition frequency f_T
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Package

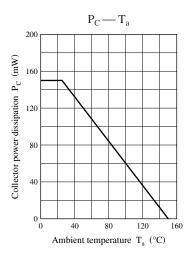
- Code SMini3-F2
- Marking Symbo

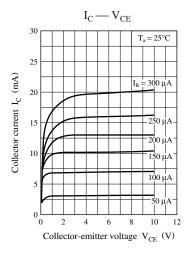
■ Absolute Maximum Ratings $T_a = 25$ °C

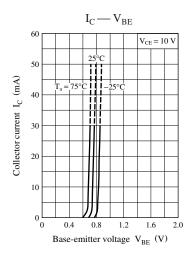
 S-Mini type package, allowing do automatic insertion through the typacking Absolute Maximum Ratings 	tape pack	ing and the		• M • Pi 1 2	Mini3-F2 larking S in Name . Base . Emitter	ymb o	10
Parameter	Symbol	Rating	Unit	al of our	4770)	
Collector-base voltage (Emitter open)	V _{CBO}	15	V	400	.ec		S.
Collector-emitter voltage (Base open)	V _{CEO}	12	V	10, 97	9	ردير وال)
Emitter-base voltage (Collector open)	V_{EBO}	2.5	5.V	S. Co			
Collector current	I_C	30	mA	70	S		
Peak collector current	I_{CP}	20	(GiA	(O)	-2/6		
Collector power dissipation	P _C	×0150 Q	mW		50		
Junction temperature	T _j	150	€	On			
Storage temperature	T _{stg}	-85 to +150	o °C	-CV			
■ Electrical Characteristics T	25°C	743°C	CO	40			
Parameter, 0	Symbo	7,00	Conditio	ns	Min	Тур	Max

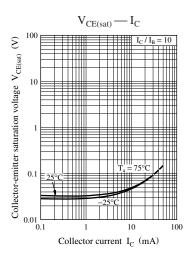
Parameter, 0	Symbol	700	conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	СВО	$V_{CB} = 1$	$V, I_E = 0$			100	nA
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 2$	$V, I_C = 0$			1	μΑ
Forward current transfer ratio	$h_{\rm FE}$	$\mathbf{V}_{\mathrm{CE}} = 1$	$0 \text{ V}, I_{\text{C}} = 10 \text{ mA}$	40			_
Transition frequency	f _T O	$V_{CE} = 1$	$0 \text{ V}, I_{\text{C}} = 10 \text{ mA}, f = 0.8 \text{ GHz}$		4.5		GHz
Collector output capacitance	Cob	$V_{CB} = 1$	$0 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$			1.2	pF
(Common base, input open circuited)	O.						
Forward transfer gain	$ S_{21e} ^2$	$V_{CE} = 1$	$0 \text{ V}, I_{\text{C}} = 20 \text{ mA}, f = 0.8 \text{ GHz}$	9	12		dB
Maximum unilateral power gain	G_{UM}	$V_{CE} = 1$	$0 \text{ V}, I_{\text{C}} = 20 \text{ mA}, f = 0.8 \text{ GHz}$	12	14		dB
Noise figure	NF	$V_{CE} = 1$	$0 \text{ V}, I_{\text{C}} = 5 \text{ mA}, f = 0.8 \text{ GHz}$		1.3	2.5	dB

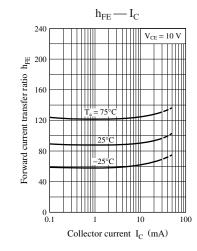
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

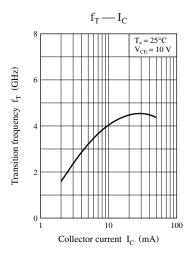


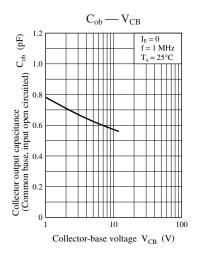


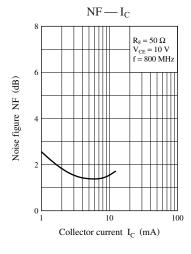


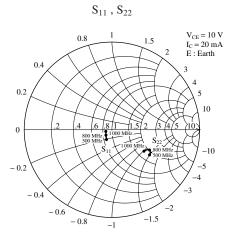




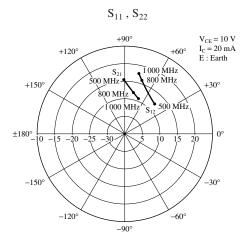






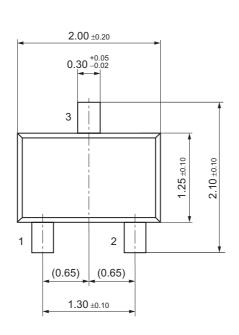


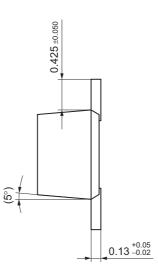
2 SJC00360AED



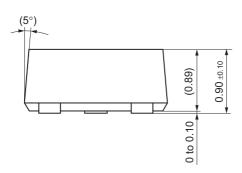
SJC00360AED 3

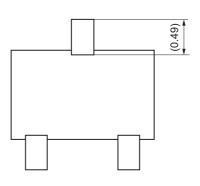
SMini3-F2 Unit: mm











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